

Application/Control Number: 10/685,873
Art Unit: 2878

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oxide (ONO) layer comprises:

thermally growing a base oxide layer on said substrate surface;

nitridizing said base oxide layer in a NH_3 ambient;

depositing a nitride layer overlying said base oxide layer; and

oxidizing said nitride layer to form a top oxide layer overlying said nitride layer.

6. The method according to Claim 5 wherein said nitride layer is a silicon-rich nitride layer.

7. The method according to Claim 5 further comprising annealing said ONO layer in NH_3 or N_2O .

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8. The method according to Claim 1 further comprising annealing said twin MONOS memory in H_2 after contact open process.

9. The method according to Claim 1 wherein when electrons stored in a nitride portion of said ONO layer are to be erased through a bottom oxide portion of said ONO layer, a bottom oxide portion is thinner than a top oxide portion of said ONO layer.

10. The method according to Claim 1 wherein when electrons stored in a nitride portion of said ONO layer are to be erased through a top oxide portion of said ONO layer, a top oxide portion is thinner than a bottom oxide portion of said ONO layer.